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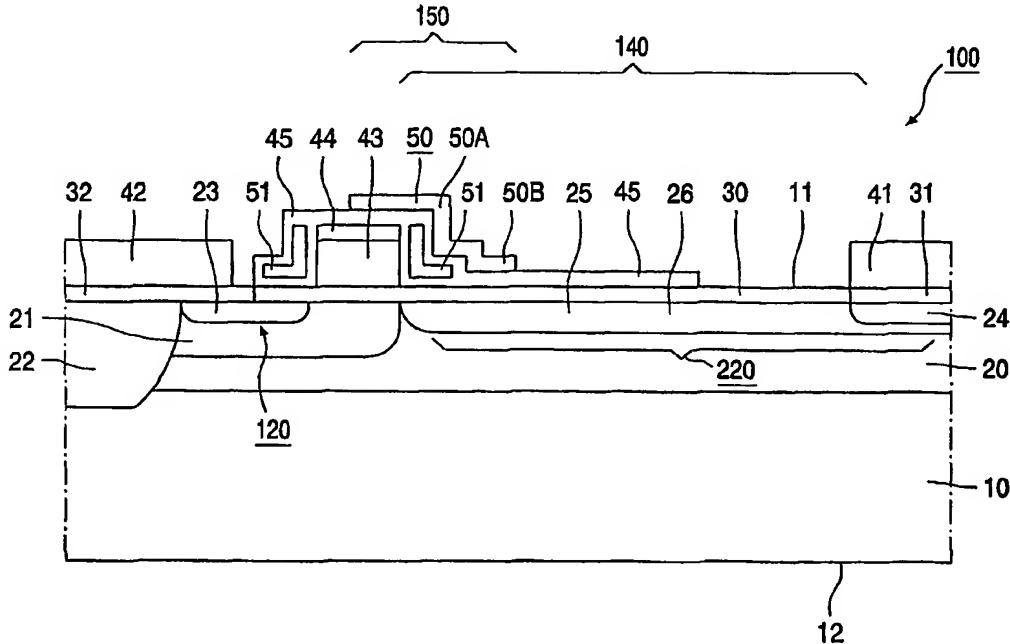
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(54) Title: ELECTRONIC DEVICE COMPRISING AN LDMOS TRANSISTOR



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(57) Abstract: The LDMOS transistor (99) of the invention is provided with a stepped shield structure (50) and/or with a first (25) and a second (26) drain extension region having a higher dopant concentration than the second drain extension region, and being covered by the shield.



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